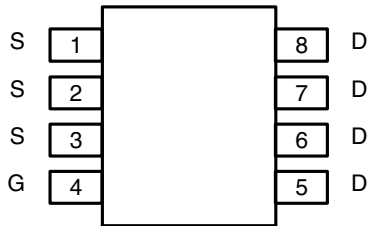


N-Channel 30 V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
30	0.0095 at V _{GS} = 10 V	16	9.5 nC
	0.0120 at V _{GS} = 4.5 V	15	

SO-8



Top View

Ordering Information:

Si4774DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

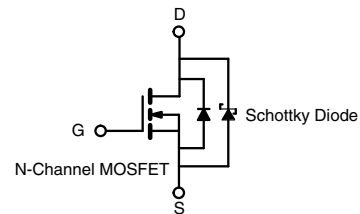
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET[®] Monolithic TrenchFET[®] Gen. III Power MOSFET and Schottky Diode
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Notebook PC
 - System Power, Memory
- Buck Converter
- Synchronous Rectifier Switch



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	16
		T _C = 70 °C	13.6
		T _A = 25 °C	12 ^{b, c}
		T _A = 70 °C	9.6 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	50	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	4.5
		T _A = 25 °C	2.3 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	15	mJ
Single Pulse Avalanche Energy	E _{AS}	11.25	
Maximum Power Dissipation	P _D	T _C = 25 °C	5
		T _C = 70 °C	3.2
		T _A = 25 °C	2.5 ^{b, c}
		T _A = 70 °C	1.6 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	38	50	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	20	25	

Notes:

a. Based on T_C = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under steady state conditions is 85 °C/W.

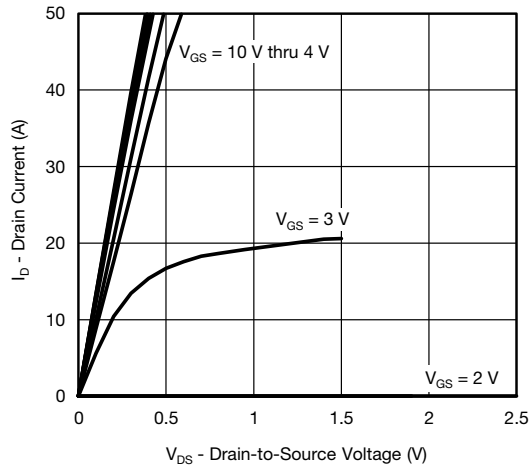
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 1 mA	30			V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 mA	1		2.3	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		0.028	0.200	mA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C		2.5	20	
On -State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		0.0079	0.0095	Ω
		V _{GS} = 4.5 V, I _D = 7 A		0.0096	0.0120	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A		43		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1025		pF
Output Capacitance	C _{oss}			251		
Reverse Transfer Capacitance	C _{rss}			100		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		20.3	30.5	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A		9.5	14.3	
Q _{gs}			2.8			
Q _{gd}			3.2			
Gate Resistance	R _g	f = 1 MHz	0.3	1.0	2.0	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		11	22	ns
Rise Time	t _r			22	48	
Turn-Off Delay Time	t _{d(off)}			13	26	
Fall Time	t _f			11	22	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		8	16	
Rise Time	t _r			13	26	
Turn-Off Delay Time	t _{d(off)}			14	28	
Fall Time	t _f			9	18	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			4.5	A
Pulse Diode Forward Current ^a	I _{SM}				50	
Body Diode Voltage	V _{SD}	I _S = 2 A		0.44	0.55	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5 A, dI/dt = 100 A/μs, T _J = 25 °C		18	35	ns
Body Diode Reverse Recovery Charge	Q _{rr}			7.5	15	nC
Reverse Recovery Fall Time	t _a			10		ns
Reverse Recovery Rise Time	t _b			8		

Notes:

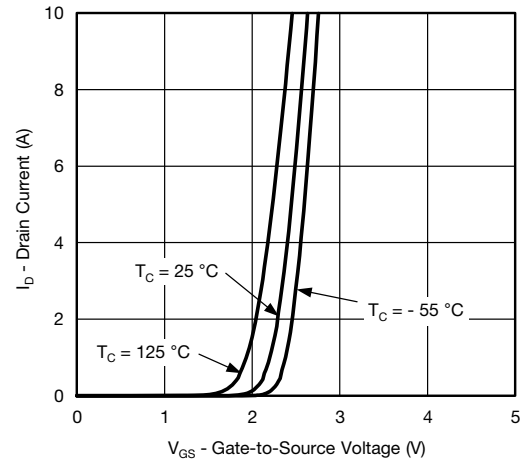
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

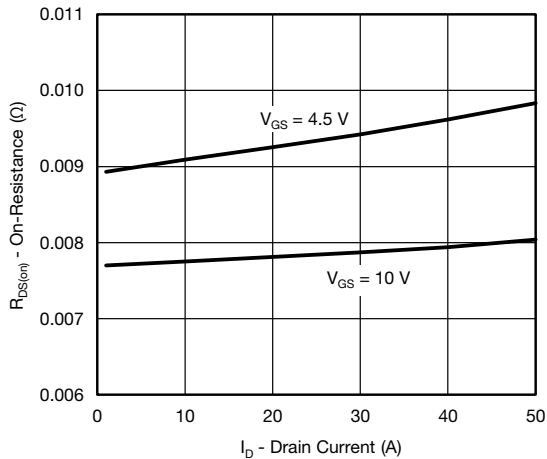
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



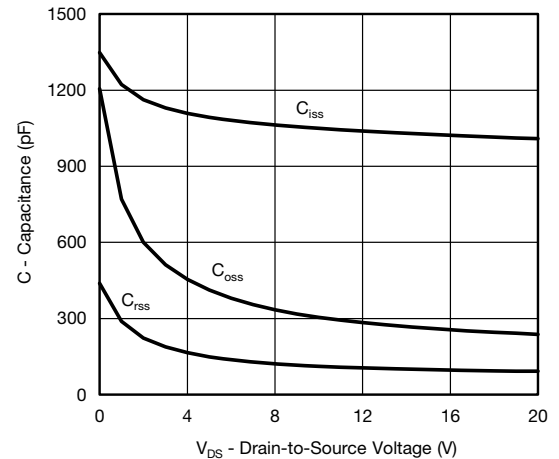
Output Characteristics



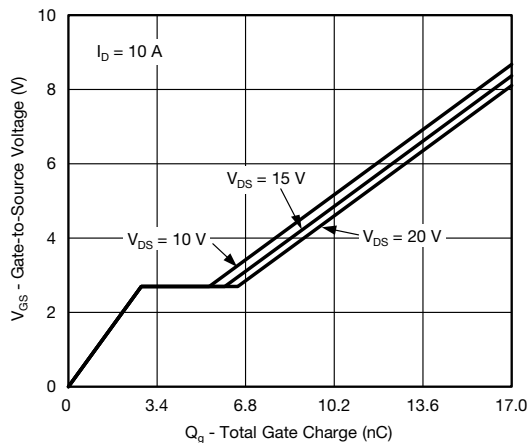
Transfer Characteristics



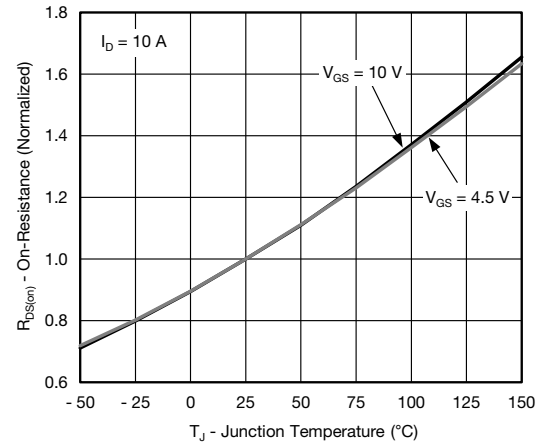
On-Resistance vs. Drain Current



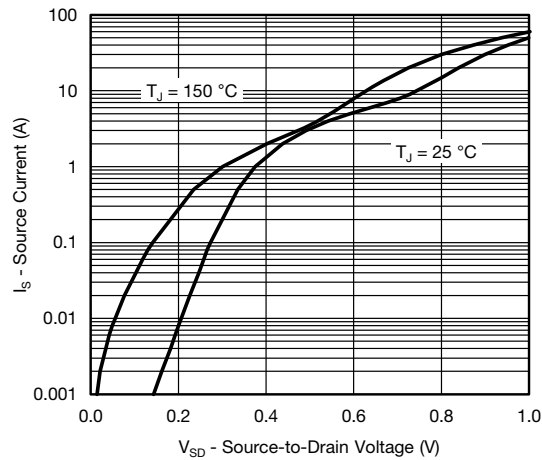
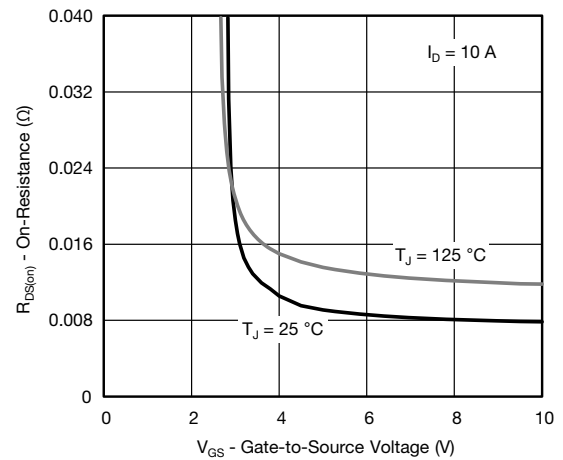
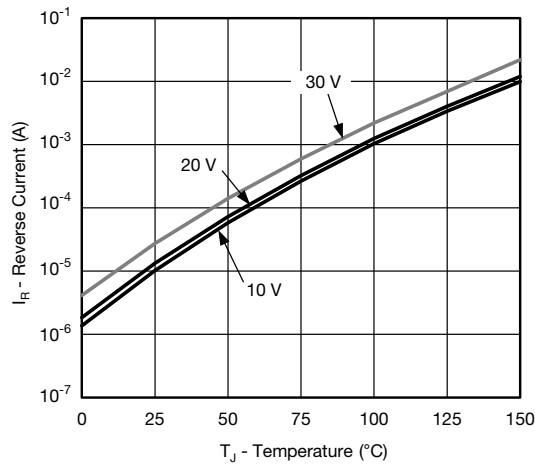
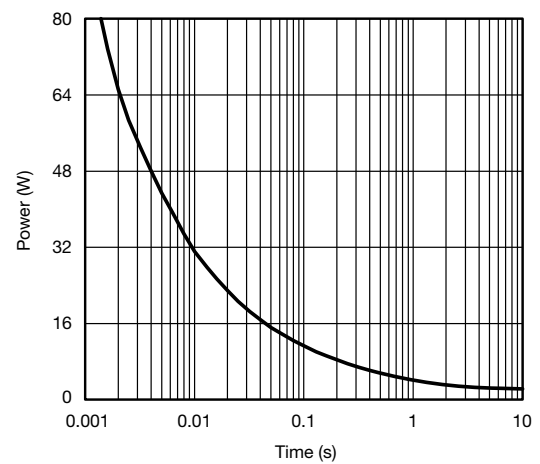
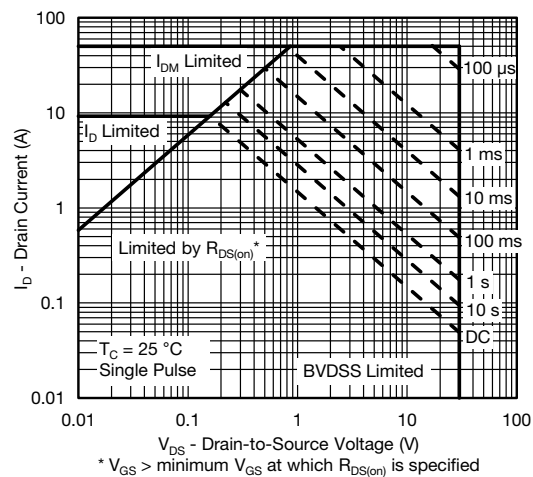
Capacitance



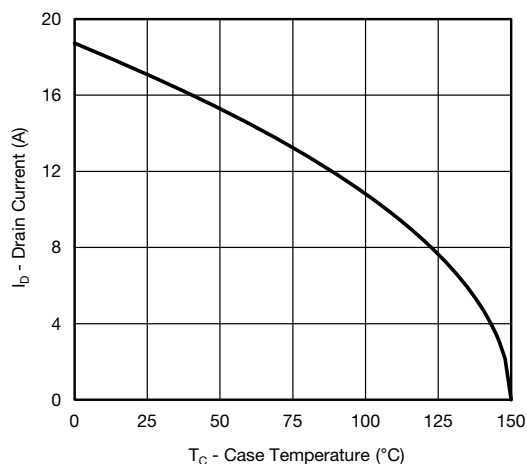
Gate Charge



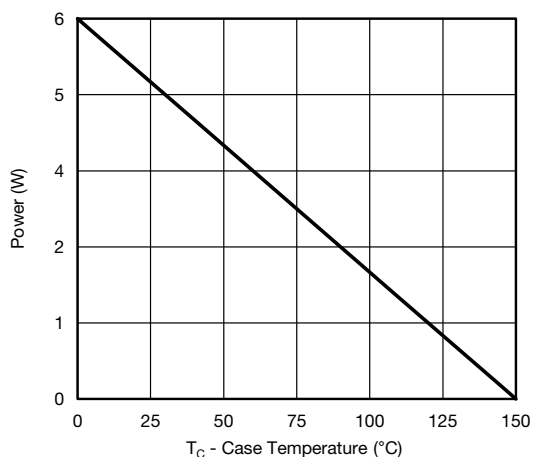
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Reverse Current (Schottky)****Single Pulse Power, Junction-to-Ambient****Safe Operating Area**

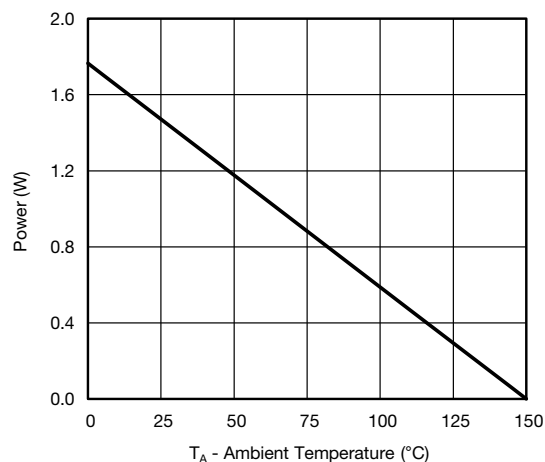
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

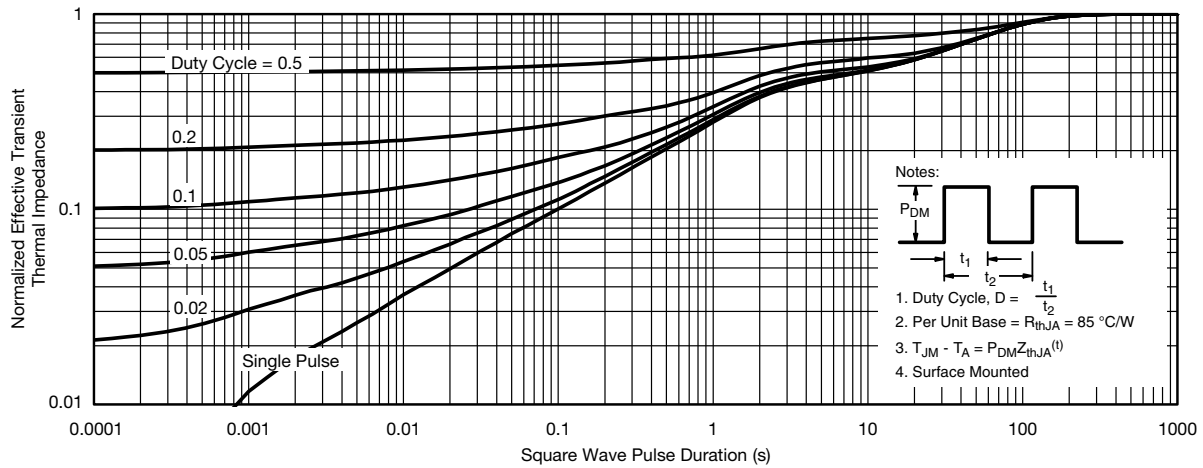
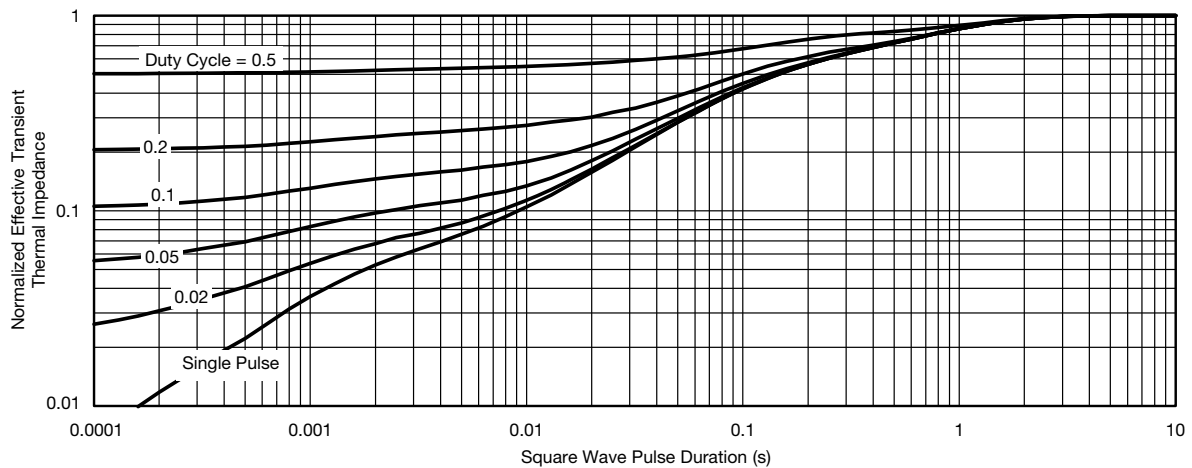


Power Derating, Junction-to-Foot



Power Derating, Junction-to-Ambient

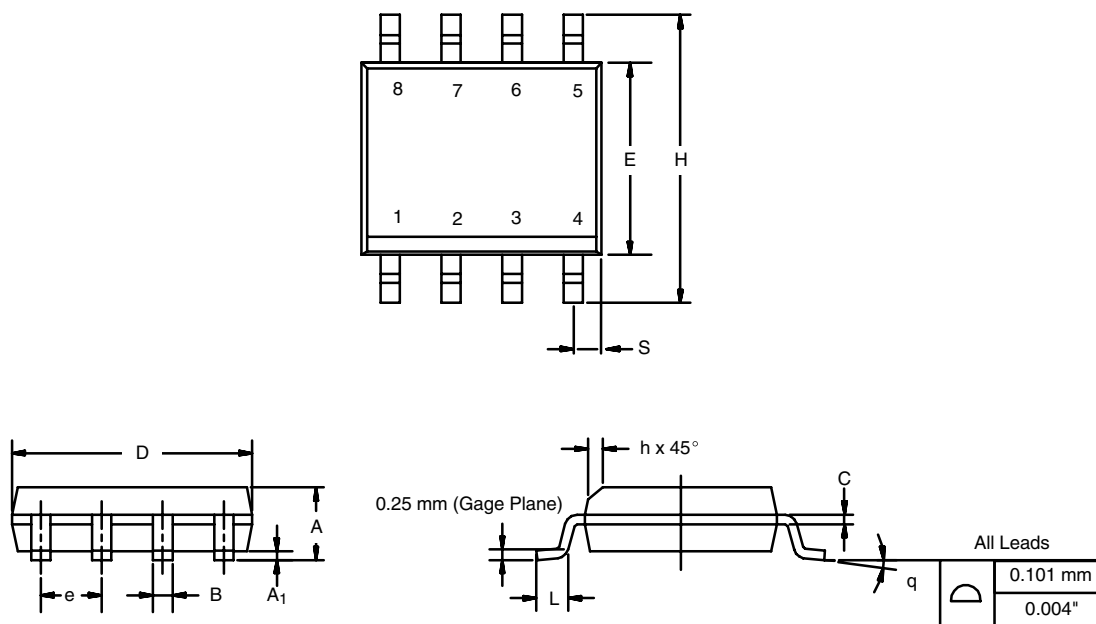
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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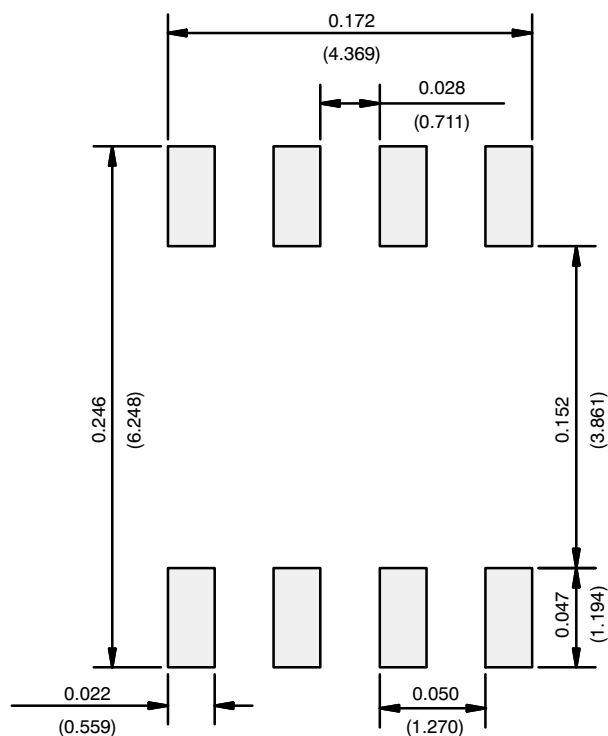
SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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